

Serial No. 10/046,607

RD-25,993-7

**Amendments to the Specification**

Please replace the paragraph beginning on page 8, line 3, and ending on page 8, line 11, of the specification with the following amended paragraph:

Second, the nozzle 8 has a wide end, i.e. opposite the anode 4, which allows the plasma to cover a relatively large area of the substrate for deposition of large areas, e.g. 10-20 centimeters in diameter. The combination of these two factors can increase the speed of deposition dramatically, e.g. up to 100 times with respect to PECVD. Additional details of the arc plasma deposition apparatus are described in commonly-owned U.S. Patent 6,213,049 Serial No. 09/033,862, entitled "Nozzle-Injector for Arc Plasma Deposition Apparatus", issued on April 10, 2001, to filed March 3, 1998, by Barry Yang, which is hereby incorporated by reference.

Please replace the paragraph beginning on page 14, line 8, and ending on page 14, line 29, of the specification with the following amended paragraph:

Examples of materials which can be injected into the plasma to form the UV absorbing layer include organometallic compounds containing zinc, titanium, or cerium, for example. Organometallic compound refers to an organic compound comprising a metal attached directly to a carbon. Preferred examples of organometallic compounds include zinc-containing compounds such as diethyl zinc (DEZ) or dimethyl zinc (DMZ). Oxygen is typically injected with the zinc containing compound to oxidize the zinc to form a UV absorbing zinc oxide layer. Alternatively, sulfur can be injected with DEZ or DMZ to form a UV absorbing zinc sulfide layer. Other UV-absorbing layers may include metal oxides such as titanium dioxide (TiO<sub>2</sub>), formed from titanium isopropoxide (Ti-IPO) and oxygen, cerium dioxide (CeO<sub>2</sub>), formed from cerium IV tetrabutoxide (C<sub>16</sub>H<sub>36</sub>O<sub>4</sub>Ce) and oxygen, and ZnO doped with one of the following dopants: indium, aluminum, fluorine, boron, gallium, thallium, copper, and iron. Indium doped ZnO provides the advantages of good infrared (IR) radiation reflection, adhesion, and stability, as described in U.S. Patent 6,261,694 Serial No. [ ] (~~GE Docket No. RD-25,973~~), entitled "Infrared Reflecting Coatings", issued on July 17, 2001, to by Charles

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Iacovangelo, which is hereby incorporated by reference. Indium may suitably comprise 2 to 15 atomic percent of the total metal content of the IZO layer.

Please replace the paragraph beginning on page 30, line 12, and ending on page 30, line 18, of the specification with the following amended paragraph:

According to a further embodiment of the invention, an adhesion promoting layer of silver or aluminum can be deposited adjacent to the UV absorbing layer. A suitable silver or aluminum adhesion promoting layer is described, for example, in U.S. Patent 6,420,032 Serial No. [[ ]] (~~GE Docket No. RD-25,972~~), entitled "Adhesion Layer for Metal Oxide UV Filters", issued on July 16, 2002, to by Charles Iacovangelo, ~~filed on the same day as the present application,~~ which is hereby incorporated by reference in its entirety.

Please replace the paragraph beginning on page 30, line 19, and ending on page 30, line 25, of the specification with the following amended paragraph:

According to a still further embodiment of the invention, a silver or aluminum infrared reflecting layer can be incorporated into the multilayer article, e.g. adjacent to the UV absorbing layer, as described, for example in U.S. Patent 6,261,694 [[Serial No. ]] (~~GE Docket No. RD-25,973~~), entitled "Infrared Reflecting Coatings", issued on July 17, 2001, to by Charles Iacovangelo, ~~filed on the same day as the present application,~~ which is hereby incorporated by reference in its entirety.